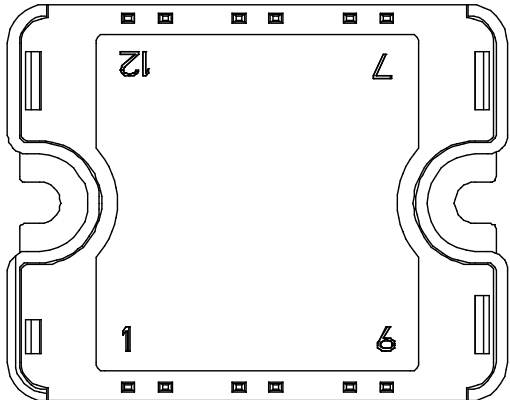
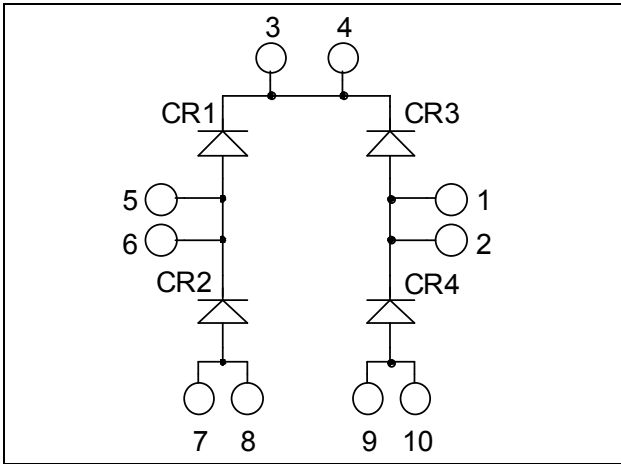


## Fast Diode Full Bridge Power Module

**$V_{RRM} = 1200V$**   
 **$I_C = 30A @ T_c = 80^\circ C$**



All multiple inputs and outputs must be shorted together  
 3/4 ; 5/6 ; 7/8 ; 1/2 ; 9/10

### Application

- Uninterruptible Power Supply (UPS)
- Induction heating
- Welding equipment
- High speed rectifiers

### Features

- Ultra fast recovery times
- Soft recovery characteristics
- High blocking voltage
- High current
- Low leakage current
- Very low stray inductance
- High level of integration

### Benefits

- Outstanding performance at high frequency operation
- Low losses
- Low noise switching
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- RoHS Compliant

### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit	
$V_R$	Maximum DC reverse Voltage	1200	V	
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage			
$I_{F(AV)}$	Maximum Average Forward Current	Duty cycle = 50%	A	
		$T_C = 25^\circ C$		43
		$T_C = 80^\circ C$	30	
$I_{FSM}$	Non-Repetitive Forward Surge Current	8.3ms	$T_J = 45^\circ C$	210

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_F$	Diode Forward Voltage	$I_F = 30\text{A}$		2.6	3.1	V
		$I_F = 60\text{A}$		3.2		
		$I_F = 30\text{A}$	$T_j = 125^\circ\text{C}$	1.8		
$I_{RM}$	Maximum Reverse Leakage Current	$V_R = 1200\text{V}$	$T_j = 25^\circ\text{C}$		100	$\mu\text{A}$
			$T_j = 125^\circ\text{C}$		500	
$C_T$	Junction Capacitance	$V_R = 200\text{V}$		36		pF

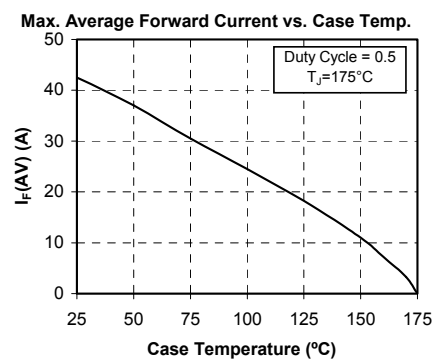
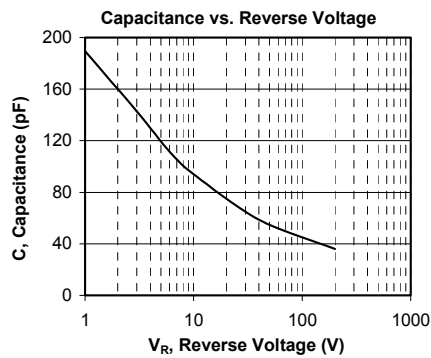
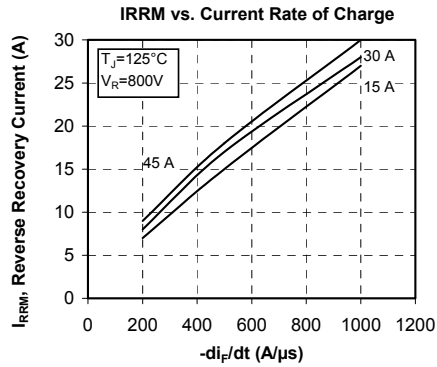
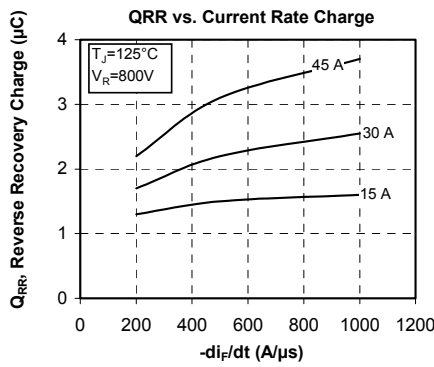
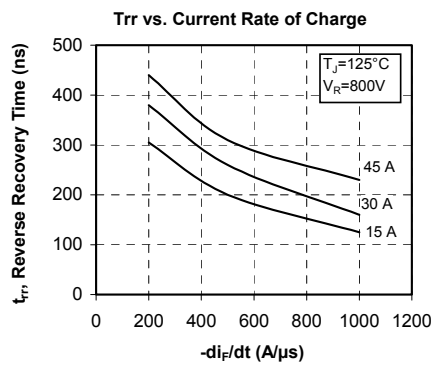
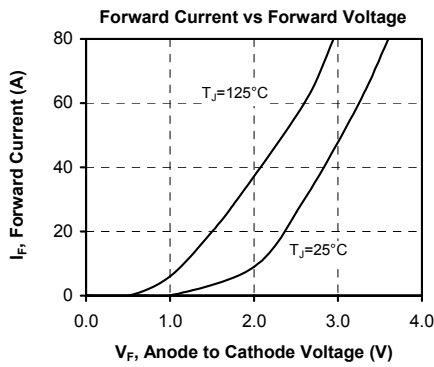
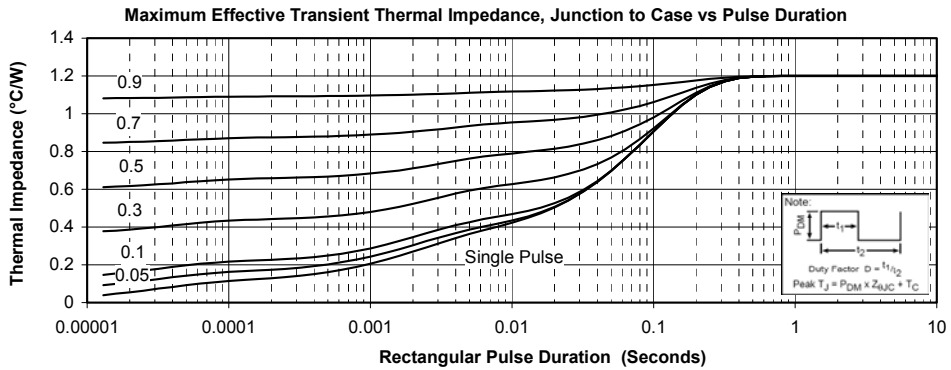
**Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$t_{rr}$	Reverse Recovery Time	$I_F = 30\text{A}$ $V_R = 800\text{V}$ $di/dt = 200\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		300	ns
			$T_j = 125^\circ\text{C}$		380	
$Q_{rr}$	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$		360	nC
			$T_j = 125^\circ\text{C}$		1700	
$I_{RRM}$	Reverse Recovery Current		$T_j = 25^\circ\text{C}$		4	A
			$T_j = 125^\circ\text{C}$		8	
$t_{rr}$	Reverse Recovery Time	$I_F = 30\text{A}$ $V_R = 800\text{V}$ $di/dt = 1000\text{A}/\mu\text{s}$	$T_j = 125^\circ\text{C}$		160	ns
$Q_{rr}$	Reverse Recovery Charge				2550	nC
$I_{RRM}$	Reverse Recovery Current				28	A

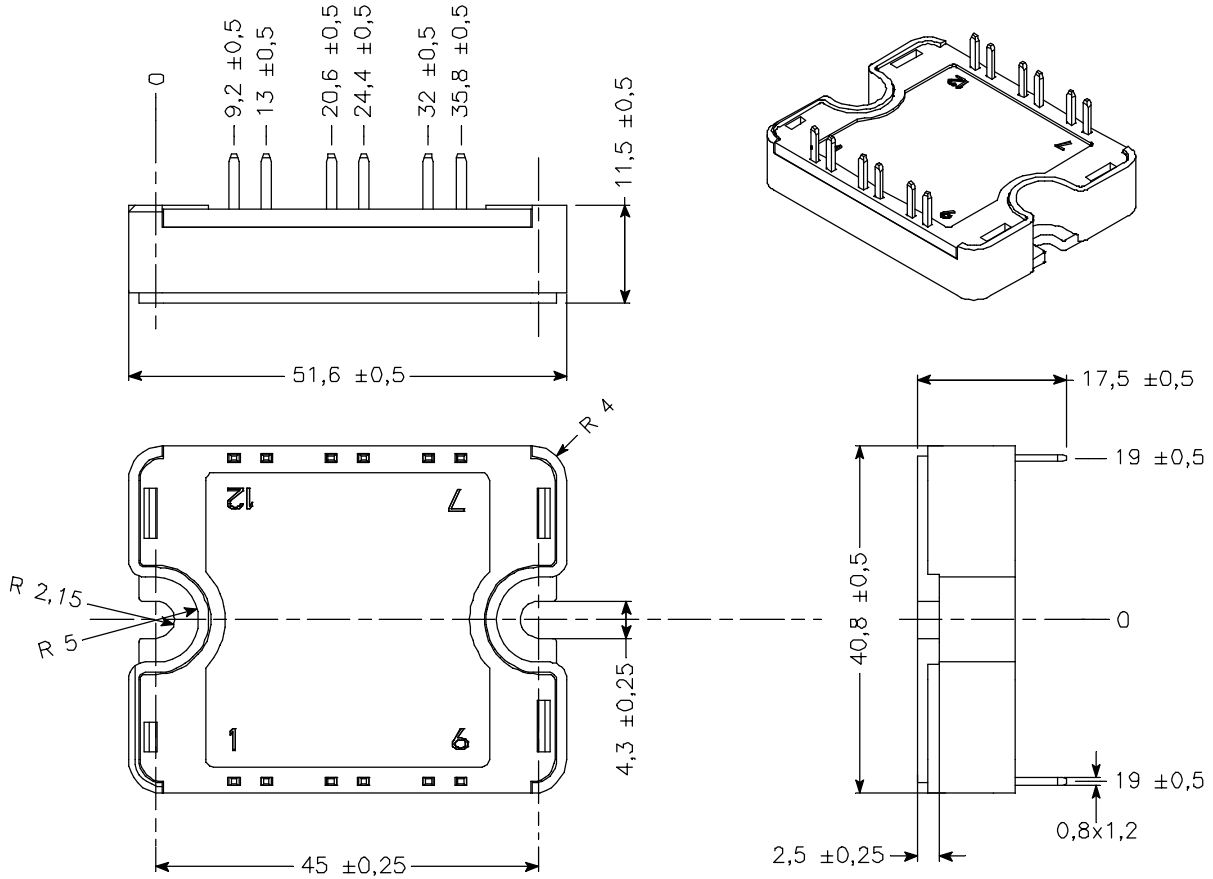
**Thermal and package characteristics**

Symbol	Characteristic	Min	Typ	Max	Unit	
$R_{thJC}$	Junction to Case Thermal Resistance			1.2	$^\circ\text{C}/\text{W}$	
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case $t = 1\text{ min}$ , $I_{isol} < 1\text{mA}$ , 50/60Hz	2500			V	
$T_j$	Operating junction temperature range	-40		175	$^\circ\text{C}$	
$T_{STG}$	Storage Temperature Range	-40		125		
$T_C$	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M4	2.5	4.7	N.m
Wt	Package Weight				80	g

## Typical Performance Curve



**SP1 Package outline** (dimensions in mm)



See application note 1904 - Mounting Instructions for SP1 Power Modules on [www.microsemi.com](http://www.microsemi.com)

Microsemi reserves the right to change, without notice, the specifications and information contained herein

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